



## P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ.)
- 30	0.0033 at V <sub>GS</sub> = - 10 V	- 36	90 nC
	0.0046 at V <sub>GS</sub> = - 4.5 V	- 29	

### FEATURES

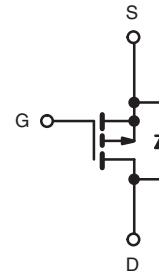
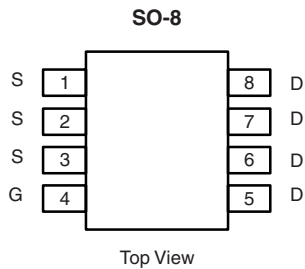
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Adaptor Switch
- High Current Load Switch
- Notebook



Ordering Information: Si4497DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 30	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 36	A
		T <sub>C</sub> = 70 °C	- 29	
		T <sub>A</sub> = 25 °C	- 24.8 <sup>a, b</sup>	
		T <sub>A</sub> = 70 °C	- 19.2 <sup>a, b</sup>	
Pulsed Drain Current	I <sub>DM</sub>	- 70		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	- 6.5	
		T <sub>A</sub> = 25 °C	- 2.9 <sup>a, b</sup>	
Avalanche Current	I <sub>AS</sub>	- 30		
Single-Pulse Avalanche Energy	E <sub>AS</sub>	45	mJ	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	7.8	W
		T <sub>C</sub> = 70 °C	5.0	
		T <sub>A</sub> = 25 °C	3.5 <sup>a, b</sup>	
		T <sub>A</sub> = 70 °C	2.2 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a, c</sup>	R <sub>thJA</sub>	29	35	°C/W	
Maximum Junction-to-Foot	R <sub>thJF</sub>	13	16		

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 80 °C/W.
- Based on T<sub>C</sub> = 25 °C.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-26		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		5.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		0.0027	0.0033	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -15\text{ A}$		0.0038	0.0046	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -20\text{ A}$		75		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		9685		pF
Output Capacitance	$C_{oss}$		995			
Reverse Transfer Capacitance	$C_{rss}$		995			
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		190	285	nC
			90	135		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		27.5		nC
Gate-Drain Charge	$Q_{gd}$		26.5			
Gate Resistance	$R_g$		$f = 1\text{ MHz}$	0.5	2.3	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		19	35	ns
Rise Time	$t_r$		13	25		
Turn-Off Delay Time	$t_{d(off)}$		115	200		
Fall Time	$t_f$		25	50		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		100	180	ns
Rise Time	$t_r$		75	150		
Turn-Off Delay Time	$t_{d(off)}$		100	180		
Fall Time	$t_f$		42	80		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-36	A
Pulse Diode Forward Current	$I_{SM}$				-70	
Body Diode Voltage	$V_{SD}$	$I_S = -3\text{ A}, V_{GS} = 0\text{ V}$		-0.70	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		31	60	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		23	45	nC	
Reverse Recovery Fall Time	$t_a$		13		ns	
Reverse Recovery Rise Time	$t_b$		18			

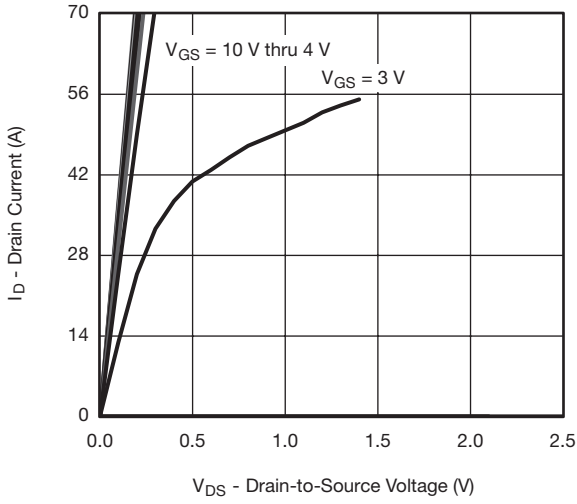
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

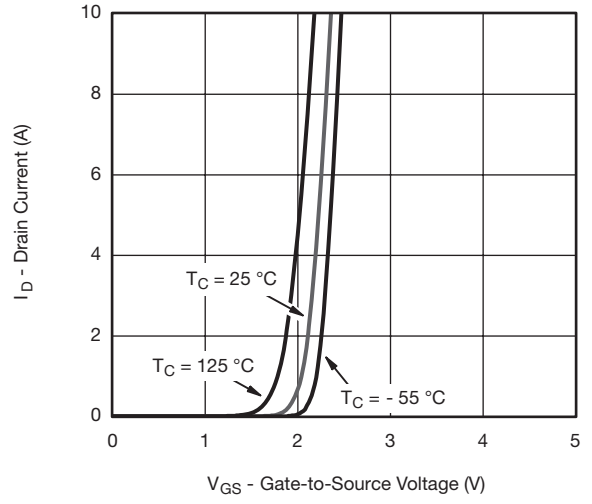
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



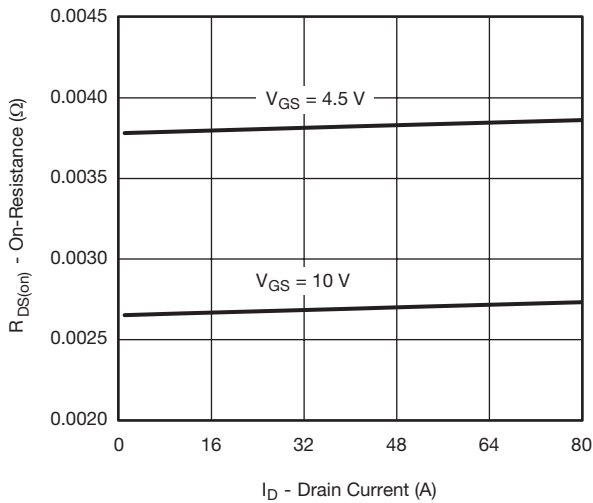
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



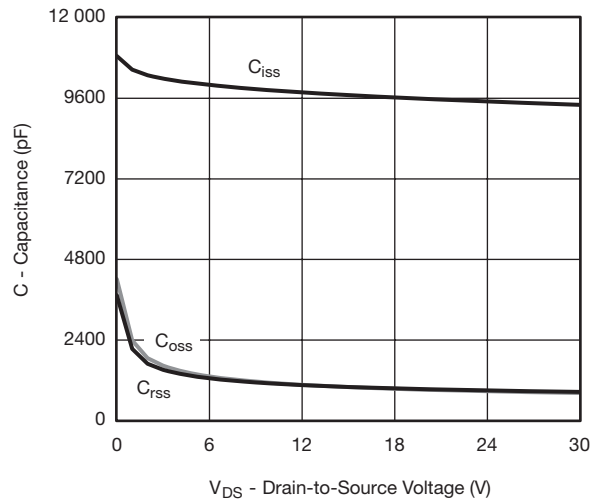
**Output Characteristics**



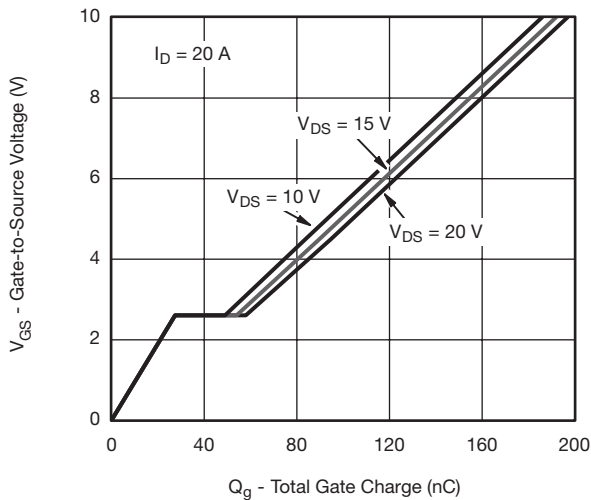
**Transfer Characteristics**



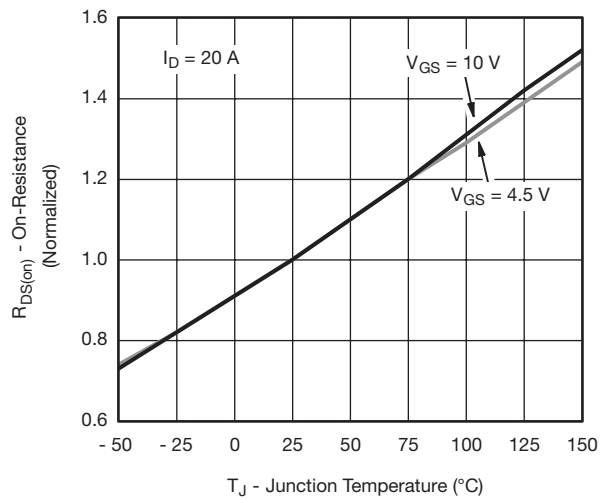
**On-Resistance vs. Drain Current**



**Capacitance**



**Gate Charge**



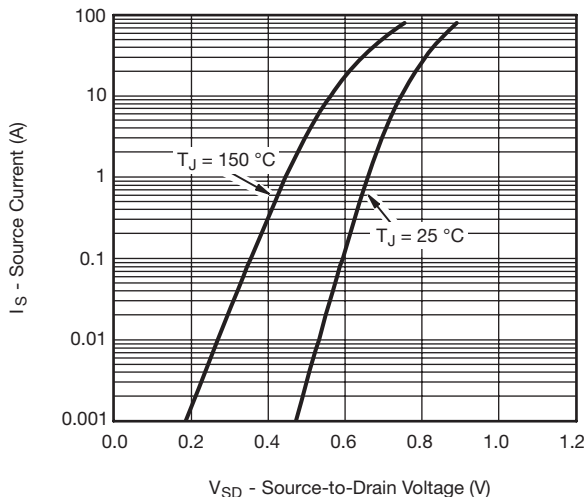
**On-Resistance vs. Junction Temperature**

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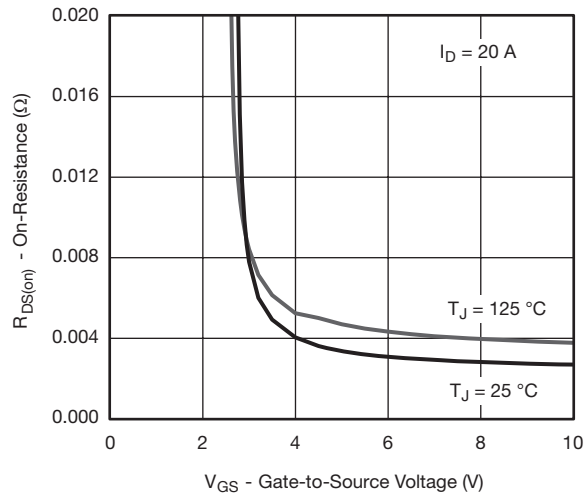
Vishay Siliconix



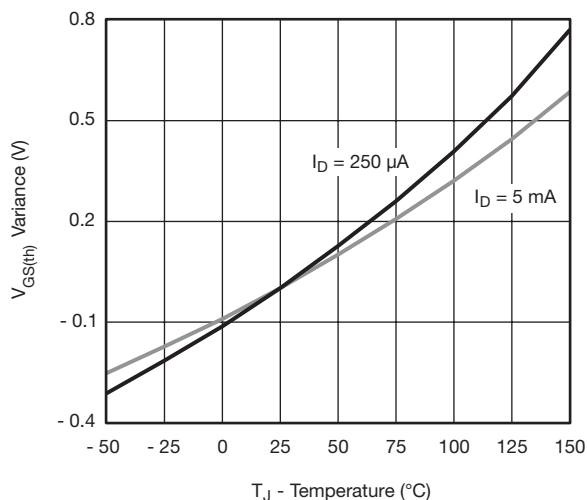
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



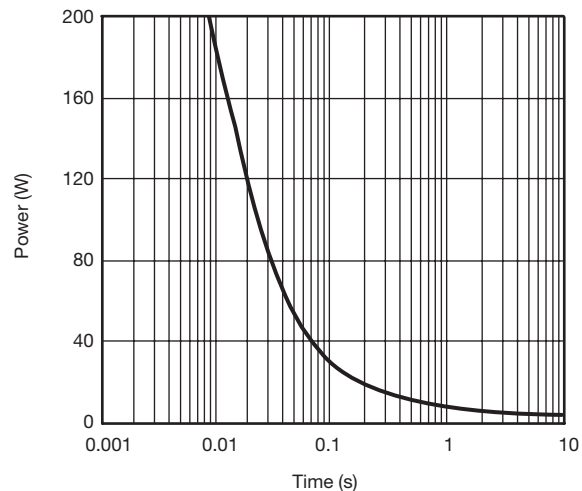
Source-Drain Diode Forward Voltage



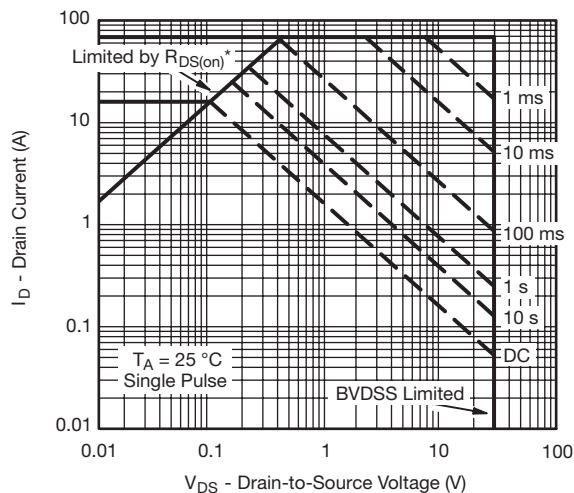
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

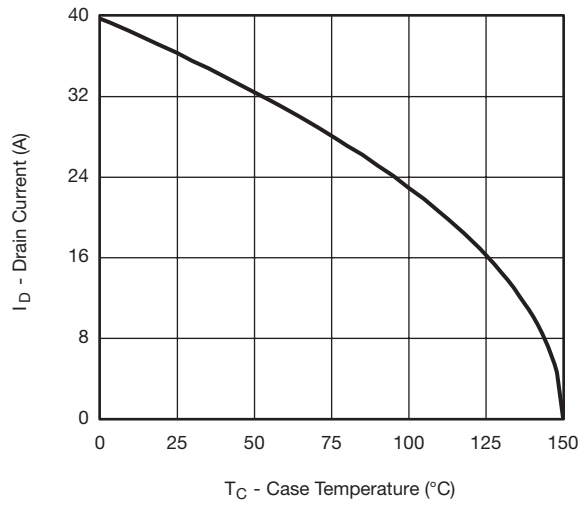


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

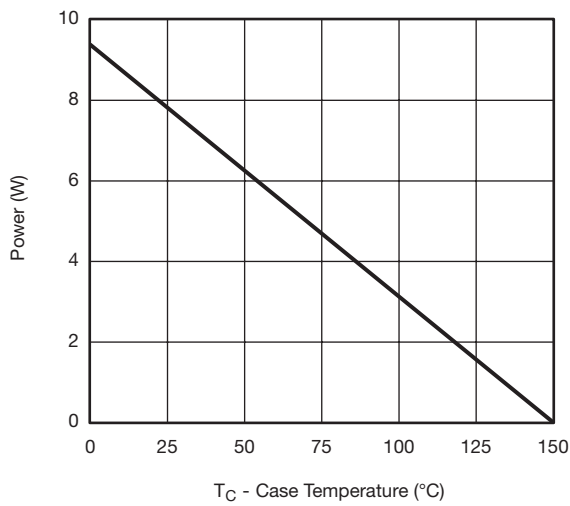
Safe Operating Area



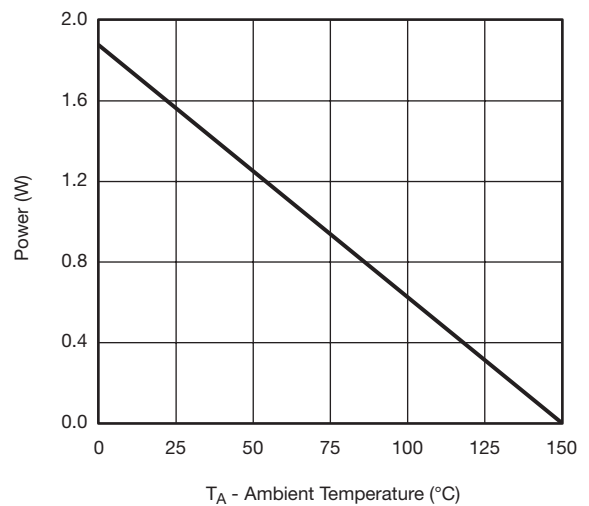
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Current Derating\***



**Power Derating, Junction-to-Foot**



**Power Derating, Junction-to-Ambient**

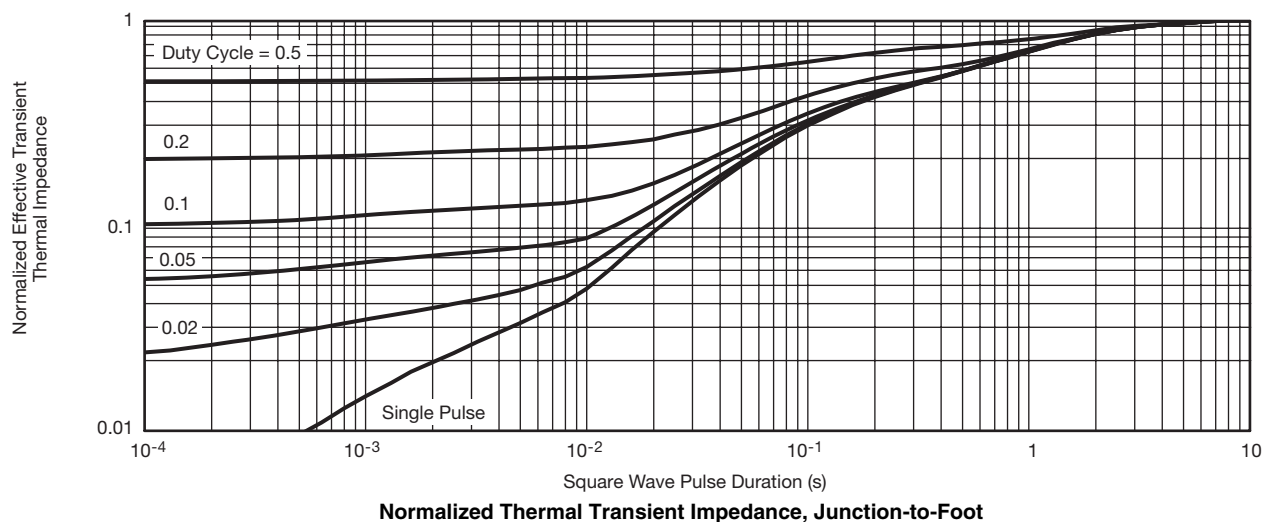
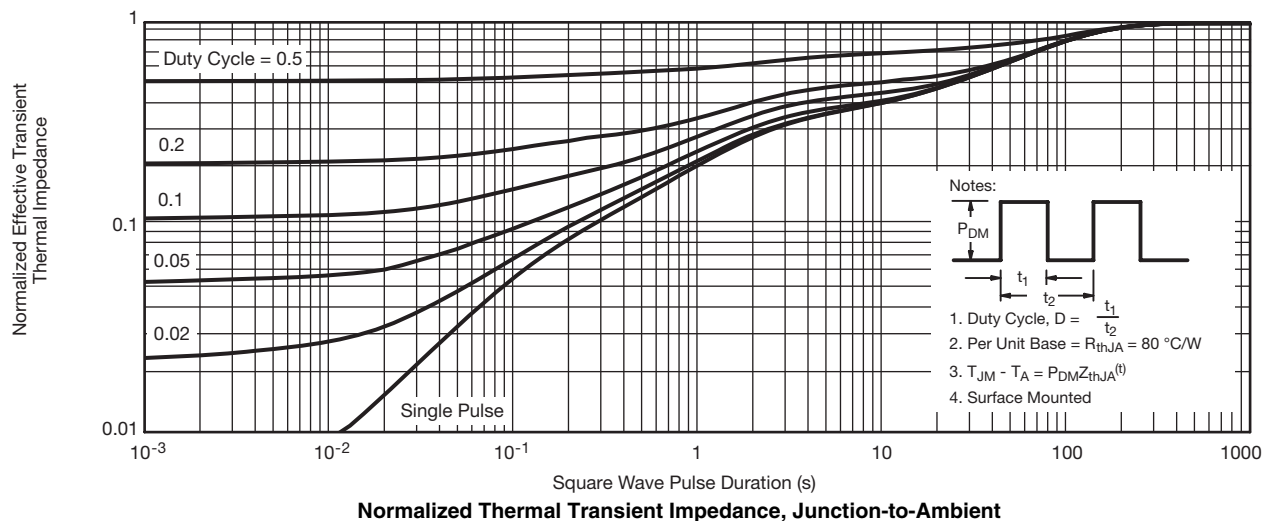
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

# Si4497DY

Vishay Siliconix



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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